

Silicon NPN Power Transistors

2SC2337

DESCRIPTION

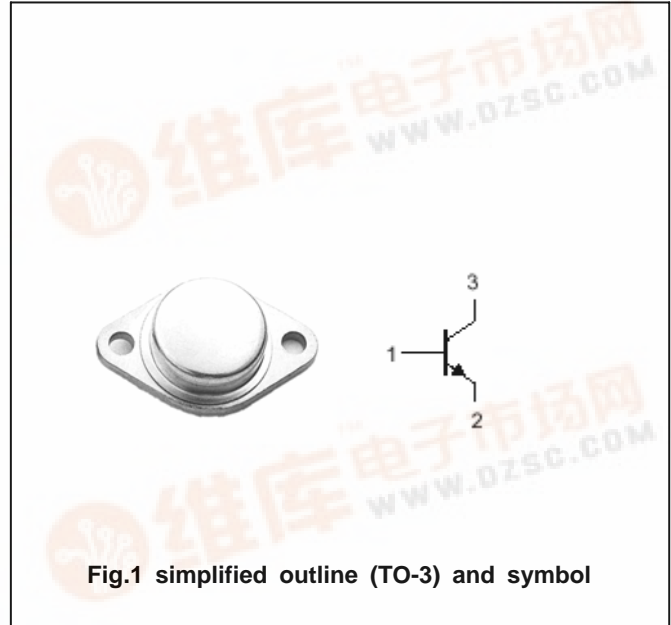
- With TO-3 package
- Complement to type 2SA1007
- Wide area of safe operation

APPLICATIONS

- For audio frequency power amplifier applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Absolute maximum ratings(Ta=°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	150	V
V _{CEO}	Collector-emitter voltage	Open base	130	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		10	A
P _C	Collector power dissipation	T _C =25°C	100	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =50mA ; I _B =0	130			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA ; I _C =0	5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =5A; I _B =0.5A			2.5	V
V _{BE}	Base-emitter on voltage	I _C =1A ; V _{CE} =5V			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =150V; I _E =0			50	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			50	μ A
h _{FE-1}	DC current gain	I _C =2A ; V _{CE} =5V	40		320	
h _{FE-2}	DC current gain	I _C =5A ; V _{CE} =5V	20			
C _{OB}	Collector output capacitance	I _E =0; V _{CB} =10V; f=1MHz		150		pF
f _T	Transition frequency	I _C =1A ; V _{CE} =10V		70		MHz

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PACKAGE OUTLINE

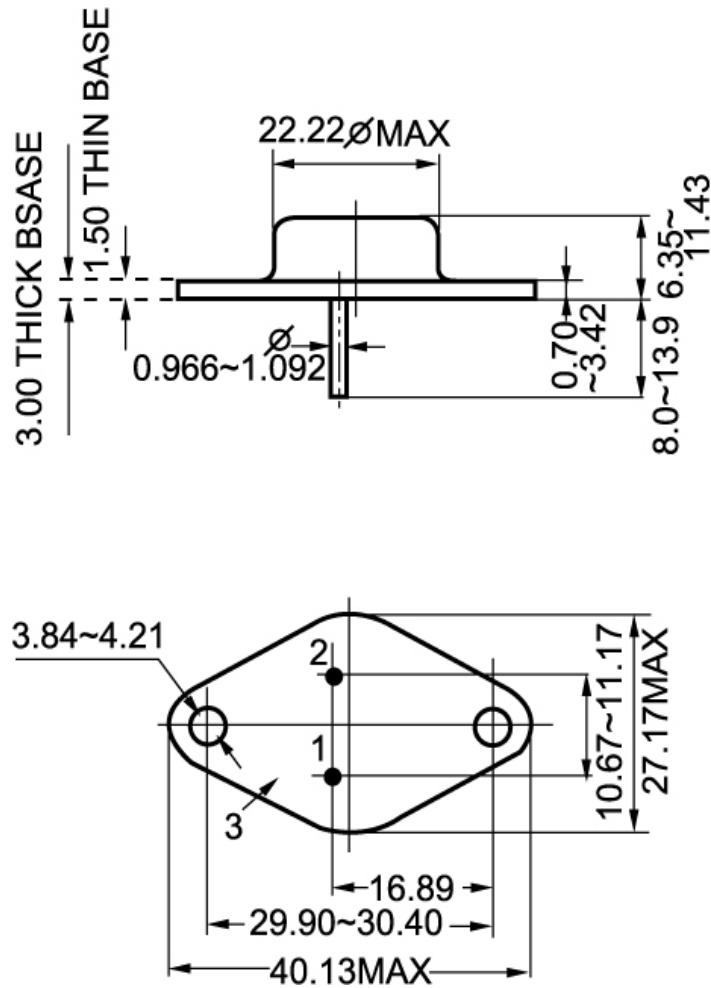


Fig.2 outline dimensions (unindicated tolerance: ± 0.1 mm)